

**BYV34-600** Dual rectifier diode ultrafast Rev. 02 — 28 September 2018

Product data sheet

#### 1. **Product profile**

## 1.1 General description

Ultrafast, dual common cathode, epitaxial rectifier diode in a SOT78 (TO-220AB) plastic package.

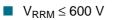
### 1.2 Features

- Fast switching
- Soft recovery characteristic
- Low switching loss

## 1.3 Applications

Output rectifiers in high frequency switched-mode power supplies

### 1.4 Quick reference data



V<sub>F</sub>  $\le$  1.16 V

Low forward voltage drop High thermal cycling performance Discontinuous Current Mode (DCM)

Low thermal resistance

- Power Factor Correction (PFC)
- I<sub>O(AV)</sub> ≤ 20 A t<sub>rr</sub> ≤ 60 ns

#### **Pinning information** 2.

#### Table 1. **Pinning**

|     | 5                      |                    |          |
|-----|------------------------|--------------------|----------|
| Pin | Description            | Simplified outline | Symbol   |
| 1   | anode 1                |                    |          |
| 2   | cathode                | mb                 |          |
| 3   | anode 2                | <u>ک</u> ک         |          |
| mb  | mounting base; cathode |                    | _ sym084 |

23 SOT78 (3-lead TO-220AB)

1

## 3. Ordering information

| Table 2. Ordering information |          |  |         |  |  |  |  |  |  |
|-------------------------------|----------|--|---------|--|--|--|--|--|--|
| Type number                   | Package  |  |         |  |  |  |  |  |  |
|                               | Name     | Description  | Version |  |  |  |  |  |  |
| BYV34-600                     | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |  |  |  |  |  |  |

# 4. Limiting values

### Table 3.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                              | Conditions   | Min | Мах  | Unit |
|--------------------|--|--|-----|------|------|
| V <sub>RRM</sub>   | repetitive peak reverse voltage        |  | -   | 600  | V    |
| V <sub>RWM</sub>   | crest working reverse voltage          |  | -   | 600  | V    |
| V <sub>R</sub>     | reverse voltage                        | square waveform; $\delta$ = 1.0;<br>T <sub>mb</sub> $\leq$ 138 °C                            | -   | 600  | V    |
| I <sub>O(AV)</sub> | average output current                 | square waveform; $\delta$ = 0.5;<br>T <sub>mb</sub> $\leq$ 107 °C; both diodes conducting    | -   | 20   | A    |
| I <sub>FRM</sub>   | repetitive peak forward current        | t = 25 $\mu$ s; square waveform; $\delta$ = 0.5;<br>T <sub>mb</sub> $\leq$ 107 °C; per diode | -   | 20   | A    |
| I <sub>FSM</sub>   | non-repetitive peak forward<br>current | t = 10 ms; sinusoidal waveform; per<br>diode   | -   | 120  | A    |
|                    |  | t = 8.3 ms; sinusoidal waveform; per diode   | -   | 132  | A    |
| T <sub>stg</sub>   | storage temperature                    |  | -40 | +150 | °C   |
| T <sub>i</sub>     | junction temperature                   |  | -   | 150  | °C   |

## 5. Thermal characteristics

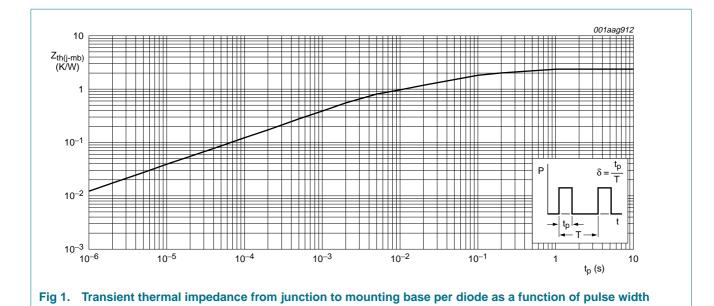
### Table 4. Thermal characteristics

| Symbol                | Parameter   | Conditions  | Min | Тур | Max | Unit |
|-----------------------|---|---|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance from junction to mounting base | with heatsink compound;<br>per diode; see <u>Figure 1</u> | -   | -   | 2.4 | K/W  |
|                       |   | with heatsink compound;<br>both diodes conducting         | -   | -   | 1.6 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance from junction to ambient       | in free air   | -   | 60  | -   | K/W  |

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## 6. Characteristics

### Table 5.Characteristics

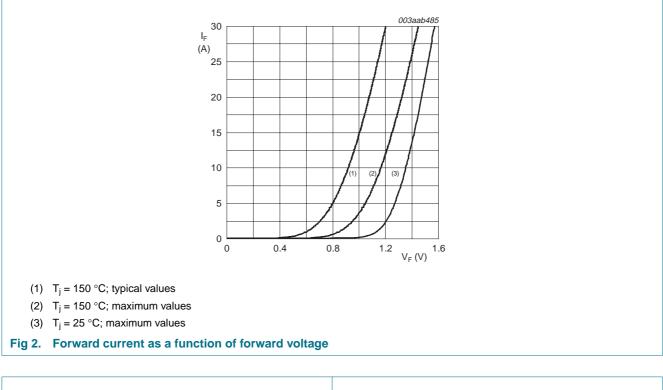
 $T_i = 25 \circ C$  unless otherwise specified.

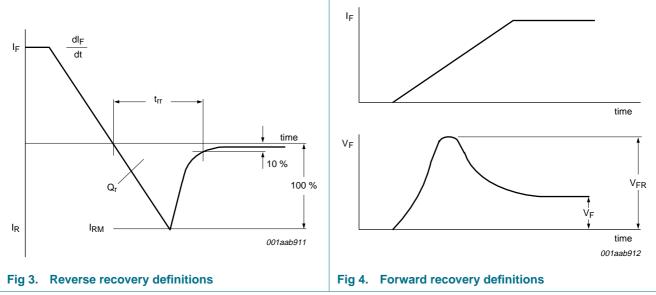
| Symbol          | Parameter                        | Conditions   | Min | Тур  | Max  | Unit |
|-----------------|----------------------------------|--|-----|------|------|------|
| Static cha      | acteristics                      |  |     |      |      |      |
| V <sub>F</sub>  | forward voltage                  | I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; see <u>Figure 2</u>  | -   | 0.92 | 1.16 | V    |
|                 |                                  | I <sub>F</sub> = 20 A; see <u>Figure 2</u>   | -   | 1.07 | 1.48 | V    |
| I <sub>R</sub>  | reverse current                  | V <sub>R</sub> = 600 V   | -   | 10   | 50   | μΑ   |
|                 |                                  | $V_{R} = 600 \text{ V}; \text{ T}_{j} = 100 ^{\circ}\text{C}$  | -   | 0.2  | 0.6  | mA   |
| Dynamic c       | haracteristics                   |  |     |      |      |      |
| Qr              | recovered charge                 | $I_F = 2 \text{ A to } V_R \ge 30 \text{ V}; \text{ d}I_F/\text{d}t = 20 \text{ A}/\mu\text{s};$ see Figure 3  | -   | 40   | 70   | nC   |
| t <sub>rr</sub> | reverse recovery time            | $I_F = 1 A \text{ to } V_R \ge 30 \text{ V};$<br>$dI_F/dt = 100 \text{ A}/\mu\text{s}; \text{ see } \frac{\text{Figure 3}}{2}$   | -   | 50   | 60   | ns   |
| I <sub>RM</sub> | peak reverse recovery<br>current | $\label{eq:l_F} \begin{array}{l} I_F = 10 \mbox{ A to } V_R \geq 30 \mbox{ V}; \\ dI_F/dt = 50 \mbox{ A}/\mu s; \mbox{ T}_j = 100 ^\circ C; \\ see \mbox{ Figure 3} \end{array}$ | -   | 3    | 5    | A    |
| V <sub>FR</sub> | forward recovery voltage         | I <sub>F</sub> = 10 A; dI <sub>F</sub> /dt = 10 A/μs;<br>see <u>Figure 4</u>   | -   | 3.2  | -    | V    |

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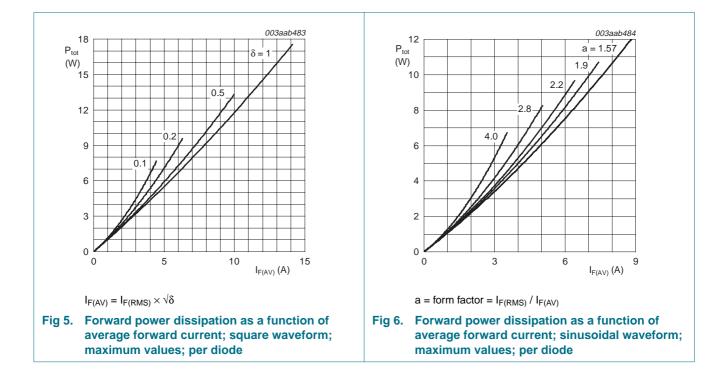




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## 7. Package outline

| $ \begin{array}{c} & & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & $ |                |                             |               |                            |              |              |                |  |      |              |                |                        |            |            |            |  |
|--|----------------|-----------------------------|---------------|----------------------------|--------------|--------------|----------------|--|------|--------------|----------------|------------------------|------------|------------|------------|--|
|  |                |                             |               |                            |              |              | 0<br>          |  | 5    | 0 mm<br>ـــا |                |                        |            |            |            |  |
| UNIT   | ONS (n<br>A    | nm are ti<br>A <sub>1</sub> | ne origi<br>b | nal dime<br>b <sub>1</sub> | nsions)<br>c | D            | D <sub>1</sub> | E  | е    | L            | L <sub>1</sub> | L <sub>2</sub><br>max. | р          | q          | Q          |  |
| mm   | 4.7<br>4.1     | 1.40<br>1.25                | 0.9<br>0.6    | 1.45<br>1.00               | 0.7<br>0.4   | 16.0<br>15.2 | 6.6<br>5.9     | 10.3<br>9.7                              | 2.54 | 15.0<br>12.8 | 3.30<br>2.79   | 3.0                    | 3.8<br>3.5 | 3.0<br>2.7 | 2.6<br>2.2 |  |
| OUTLINE  |                |                             |               |                            |              |              |                |  |      |              |                |                        |            |            | ISSUE DATE |  |
| OU<br>VEI  | TLINE<br>RSION |                             | IE            | 2                          |              | IEDEC        | 1              | IEC JEDEC JEITA<br>3-lead TO-220AB SC-46 |      |              |                |                        |            |            | 1          |  |

### Fig 7. Package outline SOT78 (3-lead TO-220AB)

# 8. Revision history

| Table 6. Revision | n history       |                         |               |             |
|-------------------|-----------------|-------------------------|---------------|-------------|
| Document ID       | Release date    | Data sheet status       | Change notice | Supersedes  |
| BYV34-600 V.2     | 20180928        | Product data sheet      | -             | BYV34-600_1 |
| Modification:     | Change from NXF | version to WeEn Version |               |             |
| BYV34-600_1       | 20071004        | Product data sheet      | -             | -           |

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## 9. Legal information

### **Data sheet status**

| Document status [1][2]               | Product<br>status [3] | Definition  |
|--------------------------------------|-----------------------|---|
| Objective<br>[short] data<br>sheet   | Development           | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification         | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production            | This document contains the product specification.   |

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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